

**IN THE CLAIMS:**

Please amend claims as follows.

1. (original) A process for producing high-resistance silicon wafers wherein it comprises subjecting silicon wafers obtained by the Czochralski method and having a resistivity of 100  $\Omega\text{cm}$  or above, an initial interstitial oxygen concentration of  $8 \times 10^{17}$  atoms/cm<sup>3</sup> or above (ASTM F 121-1979) and, further, a carbon concentration of  $5 \times 10^{15}$  to  $5 \times 10^{17}$  atoms/cm<sup>3</sup> (ASTM F 123-1981) to first heat treatment consisting in 0.5 to 5 hours of heat treatment at 850 - 1000°C employing a rate of heat-up of 0.5 to 10°C/minute at least in the temperature range of 700 - 850°C and, further, to second heat treatment consisting in 1 to 2 hours of heat treatment at 1150°C or above followed by subsequent lowering of the temperature and heat treating at 1000 - 1150°C for 2 to 10 hours.

2. (original) A process for producing high-resistance silicon wafers according to claim 1, wherein when silicon wafers having an initial interstitial oxygen concentration of  $13 \times 10^{17}$  atoms/cm<sup>3</sup> (ASTM F 121-1979) or above are used, heat treatment at 1150°C or above alone is carried out for 1 to 2 hours as the second heat treatment.

3. (currently amended) A process for producing high-resistance silicon wafers according to claim 1 [[or 2]], wherein the first heat treatment and second heat treatment are carried out successively in a non-oxidizing atmosphere.

4. (currently amended) A process for producing high-resistance silicon wafers according to ~~any of claims 1 to 3~~ claim 1, wherein, when the silicon wafers

obtained are subjected to heat treatment in the device manufacturing process, the amount of oxygen donors generated within the wafers is  $1 \times 10^{13}$  atoms/cm<sup>3</sup> or below.

5. (currently amended) A process for producing high-resistance silicon wafers according to ~~any of claims 1 to 3~~ claim 1, wherein the silicon wafers obtained have a residual oxygen concentration of  $6.5 \times 10^{17}$  atoms/cm<sup>3</sup> or above (ASTM F 121-1979) but  $13.5 \times 10^{17}$  atoms/cm<sup>3</sup> or below (ASTM F 121-1979) and, when they are subjected to heat treatment in the device manufacturing process, the amount of oxygen donors generated within the wafers is  $1 \times 10^{13}$  atoms/cm<sup>3</sup> or below.

6. (currently amended) A method of producing epitaxial wafers wherein an epitaxial layer is formed on the surface of high-resistance silicon wafers obtained by the production process according to ~~any of claims 1 to 5~~ claim 1.

7. (currently amended) A method of producing SOI wafers wherein SIMOX type SOI wafers are produced using, as base substrates, high-resistance silicon wafers obtained by the production process according to ~~any of claims 1 to 5~~ claim 1.

8. (currently amended) A method of producing SOI wafers wherein bonded type SOI wafers are produced using, as base substrate side wafers, high-resistance silicon wafers obtained by the production process according to ~~any of claims 1 to 5~~ claim 1.